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(54) SEMICONDUCTOR DEVICE AND METHOD OF
MANUFACTURING THE SAME, AND METHOD
OF FORMING INSULATION FILM

(57) Abstract:

PROBLEM TO BE SOLVED: To increase the resistance with respect to various chemicals and plasma used in semiconductor manufacturing processes by improving the adhesiveness of a low-density film having low permittivity.

SOLUTION: The surface of the low-density film, having a low permittivity, is plasma-treated to form a very fine surface modified layer.

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